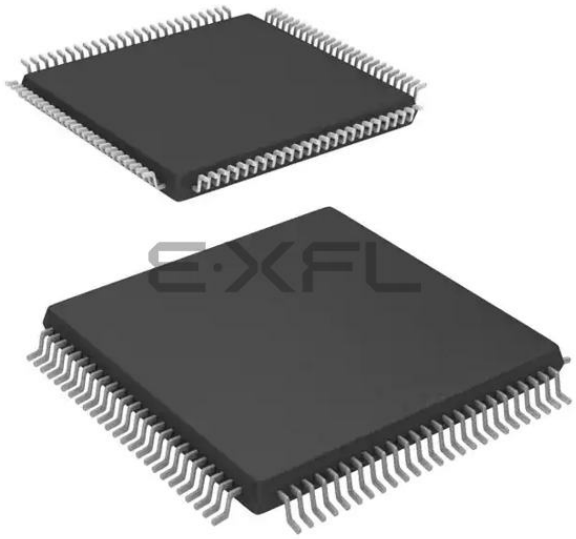

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	72
Number of Logic Elements/Cells	576
Total RAM Bits	6144
Number of I/O	66
Number of Gates	31000
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	100-TQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k10atc100-2

For more information, see the following documents:

- *Configuration Devices for APEX & FLEX Devices Data Sheet*
- *BitBlaster Serial Download Cable Data Sheet*
- *ByteBlasterMV Parallel Port Download Cable Data Sheet*
- *Application Note 116 (Configuring APEX 20K, FLEX 10K & FLEX 6000 Devices)*

FLEX 10K devices are supported by Altera development systems; single, integrated packages that offer schematic, text (including AHDL), and waveform design entry, compilation and logic synthesis, full simulation and worst-case timing analysis, and device configuration. The Altera software provides EDIF 2 0 0 and 3 0 0, LPM, VHDL, Verilog HDL, and other interfaces for additional design entry and simulation support from other industry-standard PC- and UNIX workstation-based EDA tools.

The Altera software works easily with common gate array EDA tools for synthesis and simulation. For example, the Altera software can generate Verilog HDL files for simulation with tools such as Cadence Verilog-XL. Additionally, the Altera software contains EDA libraries that use device-specific features such as carry chains which are used for fast counter and arithmetic functions. For instance, the Synopsys Design Compiler library supplied with the Altera development systems include DesignWare functions that are optimized for the FLEX 10K architecture.

The Altera development systems run on Windows-based PCs and Sun SPARCstation, and HP 9000 Series 700/800 workstations.

See the *MAX+PLUS II Programmable Logic Development System & Software Data Sheet* for more information.

Functional Description

Each FLEX 10K device contains an embedded array to implement memory and specialized logic functions, and a logic array to implement general logic.

The embedded array consists of a series of EABs. When implementing memory functions, each EAB provides 2,048 bits, which can be used to create RAM, ROM, dual-port RAM, or first-in first-out (FIFO) functions. When implementing logic, each EAB can contribute 100 to 600 gates towards complex logic functions, such as multipliers, microcontrollers, state machines, and DSP functions. EABs can be used independently, or multiple EABs can be combined to implement larger functions.

The programmable flipflop in the LE can be configured for D, T, JK, or SR operation. The clock, clear, and preset control signals on the flipflop can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinatorial functions, the flipflop is bypassed and the output of the LUT drives the output of the LE.

The LE has two outputs that drive the interconnect; one drives the local interconnect and the other drives either the row or column FastTrack Interconnect. The two outputs can be controlled independently. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, can improve LE utilization because the register and the LUT can be used for unrelated functions.

The FLEX 10K architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. The carry chain supports high-speed counters and adders; the cascade chain implements wide-input functions with minimum delay. Carry and cascade chains connect all LEs in an LAB and all LABs in the same row. Intensive use of carry and cascade chains can reduce routing flexibility. Therefore, the use of these chains should be limited to speed-critical portions of a design.

Carry Chain

The carry chain provides a very fast (as low as 0.2 ns) carry-forward function between LEs. The carry-in signal from a lower-order bit drives forward into the higher-order bit via the carry chain, and feeds into both the LUT and the next portion of the carry chain. This feature allows the FLEX 10K architecture to implement high-speed counters, adders, and comparators of arbitrary width efficiently. Carry chain logic can be created automatically by the Compiler during design processing, or manually by the designer during design entry. Parameterized functions such as LPM and DesignWare functions automatically take advantage of carry chains.

Carry chains longer than eight LEs are automatically implemented by linking LABs together. For enhanced fitting, a long carry chain skips alternate LABs in a row. A carry chain longer than one LAB skips either from even-numbered LAB to even-numbered LAB, or from odd-numbered LAB to odd-numbered LAB. For example, the last LE of the first LAB in a row carries to the first LE of the third LAB in the row. The carry chain does not cross the EAB at the middle of the row. For instance, in the EPF10K50 device, the carry chain stops at the eighteenth LAB and a new one begins at the nineteenth LAB.

Up/Down Counter Mode

The up/down counter mode offers counter enable, clock enable, synchronous up/down control, and data loading options. These control signals are generated by the data inputs from the LAB local interconnect, the carry-in signal, and output feedback from the programmable register. The Up/down counter mode uses 2 three-input LUTs: one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading. Data can also be loaded asynchronously with the clear and preset register control signals, without using the LUT resources.

Clearable Counter Mode

The clearable counter mode is similar to the up/down counter mode, but supports a synchronous clear instead of the up/down control. The clear function is substituted for the cascade-in signal in the up/down counter mode. Clearable counter mode uses 2 three-input LUTs: one generates the counter data, and the other generates the fast carry bit. Synchronous loading is provided by a 2-to-1 multiplexer. The output of this multiplexer is ANDed with a synchronous clear signal.

Internal Tri-State Emulation

Internal tri-state emulation provides internal tri-stating without the limitations of a physical tri-state bus. In a physical tri-state bus, the tri-state buffers' output enable (OE) signals select which signal drives the bus. However, if multiple OE signals are active, contending signals can be driven onto the bus. Conversely, if no OE signals are active, the bus will float. Internal tri-state emulation resolves contending tri-state buffers to a low value and floating buses to a high value, thereby eliminating these problems. The Altera software automatically implements tri-state bus functionality with a multiplexer.

Clear & Preset Logic Control

Logic for the programmable register's clear and preset functions is controlled by the DATA3, LABCTRL1, and LABCTRL2 inputs to the LE. The clear and preset control structure of the LE asynchronously loads signals into a register. Either LABCTRL1 or LABCTRL2 can control the asynchronous clear. Alternatively, the register can be set up so that LABCTRL1 implements an asynchronous load. The data to be loaded is driven to DATA3; when LABCTRL1 is asserted, DATA3 is loaded into the register.

Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across devices; it provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, an LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal will reset all IOE registers, overriding any other control signals.

Tables 8 and 9 list the sources for each peripheral control signal, and the rows that can drive global signals. These tables also show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals.

Table 10 lists the FLEX 10K row-to-IOE interconnect resources.

Table 10. FLEX 10K Row-to-IOE Interconnect Resources

Device	Channels per Row (*n*)	Row Channels per Pin (*m*)
EPF10K10 EPF10K10A	144	18
EPF10K20	144	18
EPF10K30 EPF10K30A	216	27
EPF10K40	216	27
EPF10K50 EPF10K50V	216	27
EPF10K70	312	39
EPF10K100 EPF10K100A	312	39
EPF10K130V	312	39
EPF10K250A	456	57

Column-to-IOE Connections

When an IOE is used as an input, it can drive up to two separate column channels. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the column channels. Two IOEs connect to each side of the column channels. Each IOE can be driven by column channels via a multiplexer. The set of column channels that each IOE can access is different for each IOE. See Figure 15.

ClockLock & ClockBoost Features

To support high-speed designs, selected FLEX 10K devices offer optional ClockLock and ClockBoost circuitry containing a phase-locked loop (PLL) that is used to increase design speed and reduce resource usage. The ClockLock circuitry uses a synchronizing PLL that reduces the clock delay and skew within a device. This reduction minimizes clock-to-output and setup times while maintaining zero hold times. The ClockBoost circuitry, which provides a clock multiplier, allows the designer to enhance device area efficiency by sharing resources within the device. The ClockBoost feature allows the designer to distribute a low-speed clock and multiply that clock on-device. Combined, the ClockLock and ClockBoost features provide significant improvements in system performance and bandwidth.

The ClockLock and ClockBoost features in FLEX 10K devices are enabled through the Altera software. External devices are not required to use these features. The output of the ClockLock and ClockBoost circuits is not available at any of the device pins.

The ClockLock and ClockBoost circuitry locks onto the rising edge of the incoming clock. The circuit output can only drive the clock inputs of registers; the generated clock cannot be gated or inverted.

The dedicated clock pin (`GCLK1`) supplies the clock to the ClockLock and ClockBoost circuitry. When the dedicated clock pin is driving the ClockLock or ClockBoost circuitry, it cannot drive elsewhere in the device.

In designs that require both a multiplied and non-multiplied clock, the clock trace on the board can be connected to `GCLK1`. With the Altera software, `GCLK1` can feed both the ClockLock and ClockBoost circuitry in the FLEX 10K device. However, when both circuits are used, the other clock pin (`GCLK0`) cannot be used. Figure 17 shows a block diagram of how to enable both the ClockLock and ClockBoost circuits in the Altera software. The example shown is a schematic, but a similar approach applies for designs created in AHDL, VHDL, and Verilog HDL. When the ClockLock and ClockBoost circuits are used simultaneously, the input frequency parameter must be the same for both circuits. In Figure 17, the input frequency must meet the requirements specified when the ClockBoost multiplication factor is two.

Table 13. FLEX 10K JTAG Instructions

JTAG Instruction	Description
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern output at the device pins.
EXTEST	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	Places the 1-bit bypass register between the `TDI` and `TDO` pins, which allows the BST data to pass synchronously through a selected device to adjacent devices during normal device operation.
USERCODE	Selects the user electronic signature (USERCODE) register and places it between the `TDI` and `TDO` pins, allowing the USERCODE to be serially shifted out of `TDO`.
IDCODE	Selects the IDCODE register and places it between `TDI` and `TDO`, allowing the IDCODE to be serially shifted out of `TDO`.
ICR Instructions	These instructions are used when configuring a FLEX 10K device via JTAG ports with a BitBlaster, or ByteBlasterMV or MasterBlaster download cable, or using a Jam File (**.jam**) or Jam Byte-Code File (**.jbc**) via an embedded processor.

The instruction register length of FLEX 10K devices is 10 bits. The USERCODE register length in FLEX 10K devices is 32 bits; 7 bits are determined by the user, and 25 bits are predetermined. Tables 14 and 15 show the boundary-scan register length and device IDCODE information for FLEX 10K devices.

Table 14. FLEX 10K Boundary-Scan Register Length

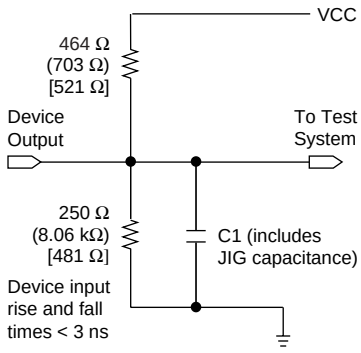
Device	Boundary-Scan Register Length
EPF10K10, EPF10K10A	480
EPF10K20	624
EPF10K30, EPF10K30A	768
EPF10K40	864
EPF10K50, EPF10K50V	960
EPF10K70	1,104
EPF10K100, EPF10K100A	1,248
EPF10K130V	1,440
EPF10K250A	1,440

Generic Testing

Each FLEX 10K device is functionally tested. Complete testing of each configurable SRAM bit and all logic functionality ensures 100% yield. AC test measurements for FLEX 10K devices are made under conditions equivalent to those shown in Figure 19. Multiple test patterns can be used to configure devices during all stages of the production flow.

Figure 19. FLEX 10K AC Test Conditions

Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result. Numbers without parentheses are for 5.0-V devices or outputs. Numbers in parentheses are for 3.3-V devices or outputs. Numbers in brackets are for 2.5-V devices or outputs.



Operating Conditions

Tables 17 through 21 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 5.0-V FLEX 10K devices.

Table 17. FLEX 10K 5.0-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	Supply voltage	With respect to ground *(2)*	–2.0	7.0	V
V_I	DC input voltage		–2.0	7.0	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	Ceramic packages, under bias		150	° C
		PQFP, TQFP, RQFP, and BGA packages, under bias		135	° C

Table 28. FLEX 10KA 3.3-V Device DC Operating Conditions *Notes (6), (7)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		1.7 or $0.5 \times V_{CCINT}$, whichever is lower		5.75	V
V_{IL}	Low-level input voltage		–0.5		$0.3 \times V_{CCINT}$	V
V_{OH}	3.3-V high-level TTL output voltage	I_{OH} = –11 mA DC, V_{CCIO} = 3.00 V *(8)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(8)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(8)*	$0.9 \times V_{CCIO}$			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(8)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(8)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(8)*	1.7			V
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 9 mA DC, V_{CCIO} = 3.00 V *(9)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(9)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(9)*			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(9)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(9)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(9)*			0.7	V
I_I	Input pin leakage current	V_I = 5.3 V to –0.3 V *(10)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.3 V to –0.3 V *(10)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load		0.3	10	mA
		V_I = ground, no load *(11)*		10		mA

Figure 22 shows the typical output drive characteristics of EPF10K10A, EPF10K30A, EPF10K100A, and EPF10K250A devices with 3.3-V and 2.5-V V_{CCIO}. The output driver is compliant with the 3.3-V ***PCI Local Bus Specification, Revision 2.2*** (with 3.3-V V_{CCIO}). Moreover, device analysis shows that the EPF10K10A, EPF10K30A, and EPF 10K100A devices can drive a 5.0-V PCI bus with eight or fewer loads.

Figure 22. Output Drive Characteristics for EPF10K10A, EPF10K30A & EPF10K100A Devices

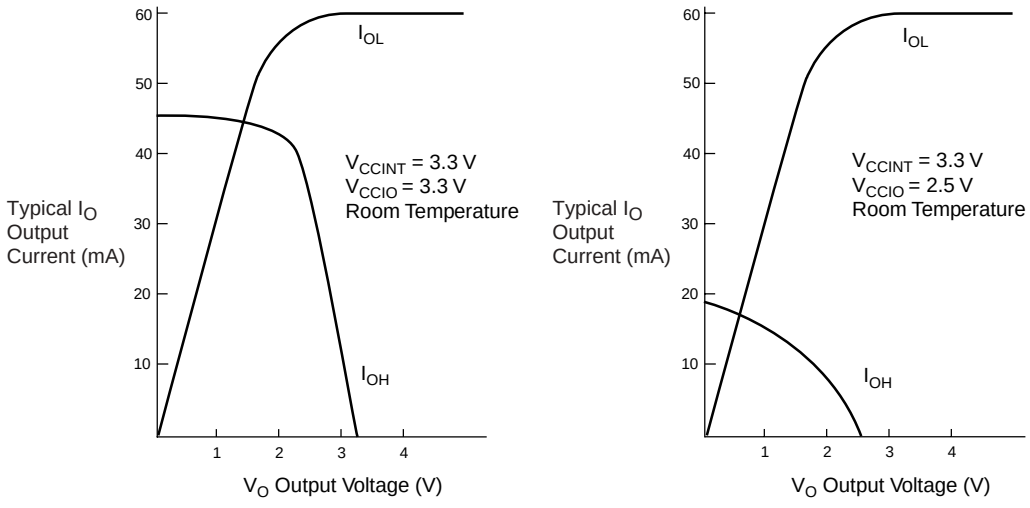


Figure 23 shows the typical output drive characteristics of the EPF10K250A device with 3.3-V and 2.5-V V_{CCIO}.

Table 32. LE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	Parameter	Conditions
t_{SU}	LE register setup time for data and enable signals before clock; LE register recovery time after asynchronous clear, preset, or load	
t_{H}	LE register hold time for data and enable signals after clock	
t_{PRE}	LE register preset delay	
t_{CLR}	LE register clear delay	
t_{CH}	Minimum clock high time from clock pin	
t_{CL}	Minimum clock low time from clock pin	

Table 33. IOE Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
t_{IOD}	IOE data delay	
t_{IOC}	IOE register control signal delay	
t_{IOCO}	IOE register clock-to-output delay	
t_{IOCOMB}	IOE combinatorial delay	
t_{IOSU}	IOE register setup time for data and enable signals before clock; IOE register recovery time after asynchronous clear	
t_{IOH}	IOE register hold time for data and enable signals after clock	
t_{IOCLR}	IOE register clear time	
t_{OD1}	Output buffer and pad delay, slow slew rate = off, $V_{CCIO} = V_{CCINT}$	C1 = 35 pF *(2)*
t_{OD2}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = low voltage	C1 = 35 pF *(3)*
t_{OD3}	Output buffer and pad delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{XZ}	IOE output buffer disable delay	
t_{ZX1}	IOE output buffer enable delay, slow slew rate = off, $V_{CCIO} = V_{CCINT}$	C1 = 35 pF *(2)*
t_{ZX2}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = low voltage	C1 = 35 pF *(3)*
t_{ZX3}	IOE output buffer enable delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{INREG}	IOE input pad and buffer to IOE register delay	
t_{IOFD}	IOE register feedback delay	
t_{INCOMB}	IOE input pad and buffer to FastTrack Interconnect delay	

Table 35. EAB Timing Macroparameters *Notes (1), (6)*		
Symbol	**Parameter**	**Conditions**
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Notes to tables:

(1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.

(2) Operating conditions: V_{CCIO} = 5.0 V ± 5% for commercial use in FLEX 10K devices.
V_{CCIO} = 5.0 V ± 10% for industrial use in FLEX 10K devices.
V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10KA devices.

(3) Operating conditions: V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10K devices.
V_{CCIO} = 2.5 V ± 0.2 V for commercial or industrial use in FLEX 10KA devices.

(4) Operating conditions: V_{CCIO} = 2.5 V, 3.3 V, or 5.0 V.

(5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the WE signal is registered.

(6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.

(7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.

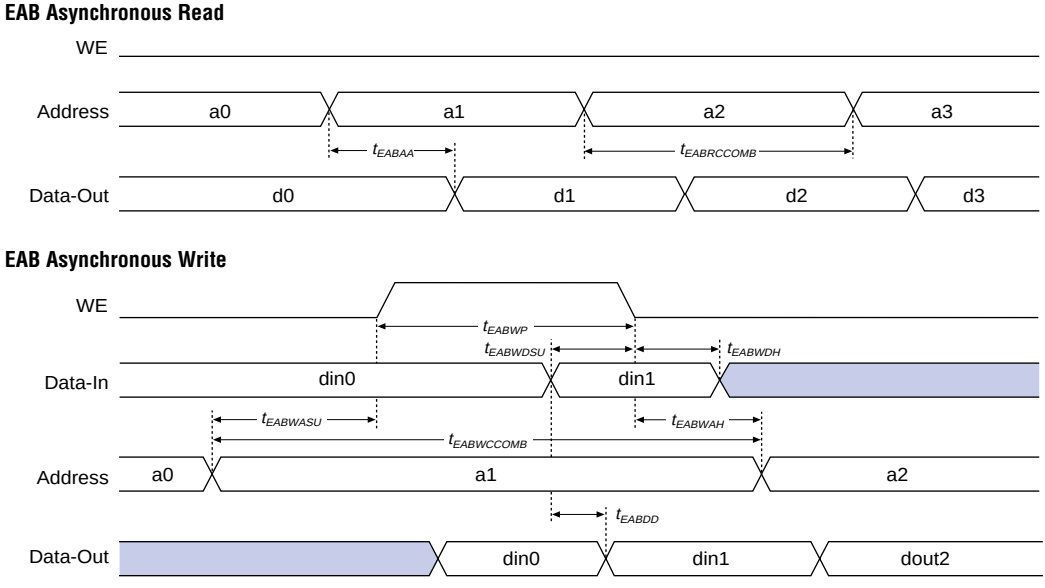
(8) External reference timing parameters are factory-tested, worst-case values specified by Altera. A representative subset of signal paths is tested to approximate typical device applications.

(9) Contact Altera Applications for test circuit specifications and test conditions.

(10) These timing parameters are sample-tested only.

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, for the EAB macroparameters in Table 34.

Figure 29. EAB Asynchronous Timing Waveforms



Tables 39 through 47 show EPF10K10 and EPF10K20 device internal and external timing parameters.

Table 39. EPF10K10 & EPF10K20 Device LE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{LUT}		1.4		1.7	ns
t_{CLUT}		0.6		0.7	ns
t_{RLUT}		1.5		1.9	ns
t_{PACKED}		0.6		0.9	ns
t_{EN}		1.0		1.2	ns
t_{CICO}		0.2		0.3	ns
t_{CGEN}		0.9		1.2	ns
t_{CGENR}		0.9		1.2	ns
t_{CASC}		0.8		0.9	ns
t_{C}		1.3		1.5	ns
t_{CO}		0.9		1.1	ns
t_{COMB}		0.5		0.6	ns
t_{SU}	1.3		2.5		ns
t_{H}	1.4		1.6		ns
t_{PRE}		1.0		1.2	ns
t_{CLR}		1.0		1.2	ns
t_{CH}	4.0		4.0		ns
t_{CL}	4.0		4.0		ns

Table 42. EPF10K10 & EPF10K20 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATACO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 64 through 70 show EPF10K100 device internal and external timing parameters.

Table 64. EPF10K100 Device LE Timing Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.5		1.5		2.0	ns
t_{CLUT}		0.4		0.4		0.5	ns
t_{RLUT}		1.6		1.6		2.0	ns
t_{PACKED}		0.9		0.9		1.3	ns
t_{EN}		0.9		0.9		1.2	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		1.1		1.1		1.4	ns
t_{CGENR}		1.2		1.2		1.5	ns
t_{CASC}		1.1		1.1		1.3	ns
t_{C}		0.8		0.8		1.0	ns
t_{CO}		1.0		1.0		1.4	ns
t_{COMB}		0.5		0.5		0.7	ns
t_{SU}	2.1		2.1		2.6		ns
t_{H}	2.3		2.3		3.1		ns
t_{PRE}		1.0		1.0		1.4	ns
t_{CLR}		1.0		1.0		1.4	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 67. EPF10K100 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		13.7		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		13.7		17.0		ns
$t_{EABRCREG}$	9.7		9.7		11.9		ns
t_{EABWP}	5.8		5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		7.3		9.0		ns
$t_{EABWCREG}$	13.0		13.0		16.0		ns
t_{EABDD}		10.0		10.0		12.5	ns
$t_{EABDATACO}$		2.0		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	5.5		5.5		5.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.5		5.8		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	2.1		2.1		2.7		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		9.5		9.5		11.8	ns

Table 100. EPF10K100A Device IOE Timing Microparameters *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{IOD}		2.5		2.9		3.4	ns
t_{IOC}		0.3		0.3		0.4	ns
t_{IOCO}		0.2		0.2		0.3	ns
t_{IOCOMB}		0.5		0.6		0.7	ns
t_{IOSU}	1.3		1.7		1.8		ns
t_{IOH}	0.2		0.2		0.3		ns
t_{IOCLR}		1.0		1.2		1.4	ns
t_{OD1}		2.2		2.6		3.0	ns
t_{OD2}		4.5		5.3		6.1	ns
t_{OD3}		6.8		7.9		9.3	ns
t_{XZ}		2.7		3.1		3.7	ns
t_{ZX1}		2.7		3.1		3.7	ns
t_{ZX2}		5.0		5.8		6.8	ns
t_{ZX3}		7.3		8.4		10.0	ns
t_{INREG}		5.3		6.1		7.2	ns
t_{IOFD}		4.7		5.5		6.4	ns
t_{INCOMB}		4.7		5.5		6.4	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 106 through 112 show EPF10K250A device internal and external timing parameters.

Table 106. EPF10K250A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.0		1.4	ns
t_{CLUT}		1.2		1.3		1.6	ns
t_{RLUT}		2.0		2.3		2.7	ns
t_{PACKED}		0.4		0.4		0.5	ns
t_{EN}		1.4		1.6		1.9	ns
t_{CICO}		0.2		0.3		0.3	ns
t_{CGEN}		0.4		0.6		0.6	ns
t_{CGENR}		0.8		1.0		1.1	ns
t_{CASC}		0.7		0.8		1.0	ns
t_{C}		1.2		1.3		1.6	ns
t_{CO}		0.6		0.7		0.9	ns
t_{COMB}		0.5		0.6		0.7	ns
t_{SU}	1.2		1.4		1.7		ns
t_{H}	1.2		1.3		1.6		ns
t_{PRE}		0.7		0.8		0.9	ns
t_{CLR}		0.7		0.8		0.9	ns
t_{CH}	2.5		3.0		3.5		ns
t_{CL}	2.5		3.0		3.5		ns

Table 109. EPF10K250A Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		6.1		6.8		8.2	ns
$t_{EABRCCOMB}$	6.1		6.8		8.2		ns
$t_{EABRCREG}$	4.6		5.1		6.1		ns
t_{EABWP}	5.6		6.4		7.5		ns
$t_{EABWCCOMB}$	5.8		6.6		7.9		ns
$t_{EABWCREG}$	15.8		17.8		21.0		ns
t_{EABDD}		5.7		6.4		7.8	ns
$t_{EABDATACO}$		0.7		0.8		1.0	ns
$t_{EABDATASU}$	4.5		5.1		5.9		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	8.2		9.3		10.9		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.7		1.8		2.1		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	0.9		0.9		1.0		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		5.3		6.0		7.4	ns